

## General Description

The WST3400S is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the small power switching and load switch applications.

The WST3400S meet the RoHS and Green Product requirement with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C<sub>dv/dt</sub> effect decline
- Green Device Available

## Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
30V	27mΩ	5.6A

## Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## SOT-23N Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	5.6	A
I <sub>D</sub> @T <sub>c</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	4.2	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	18	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1	W
P <sub>D</sub> @T <sub>A</sub> =70°C	Total Power Dissipation <sup>3</sup>	0.64	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	125	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	95	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.025	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	27	32	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	---	39	45	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	0.5	0.8	1.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.8	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	---	7	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.5	5	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	5.5	8.4	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.1	3.5	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.5	2.9	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =5A	---	2.2	4.2	ns
T <sub>r</sub>	Rise Time		---	6.8	9	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	20	40	
T <sub>f</sub>	Fall Time		---	3.5	5	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	525	600	pF
C <sub>oss</sub>	Output Capacitance		---	57	112	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	45	91	

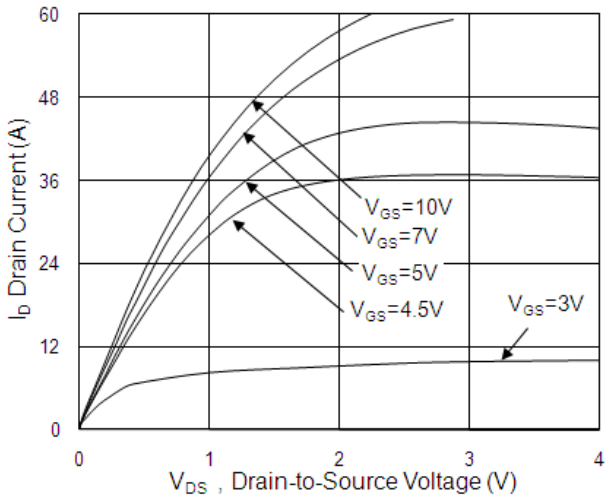
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	5.6	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	18	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =5A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	18	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	1	---	nC

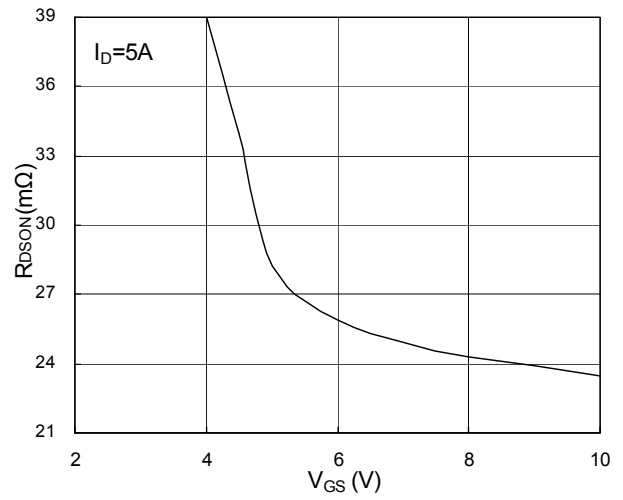
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

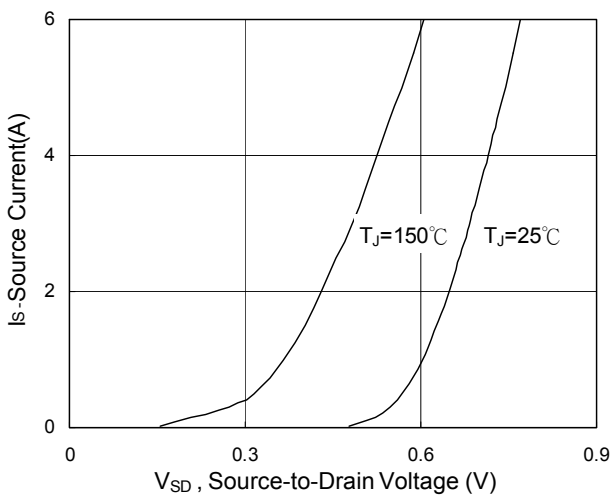
**Typical Characteristics**



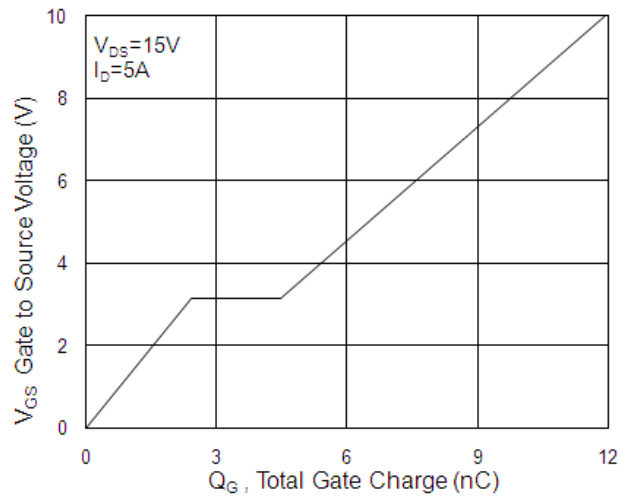
**Fig.1 Typical Output Characteristics**



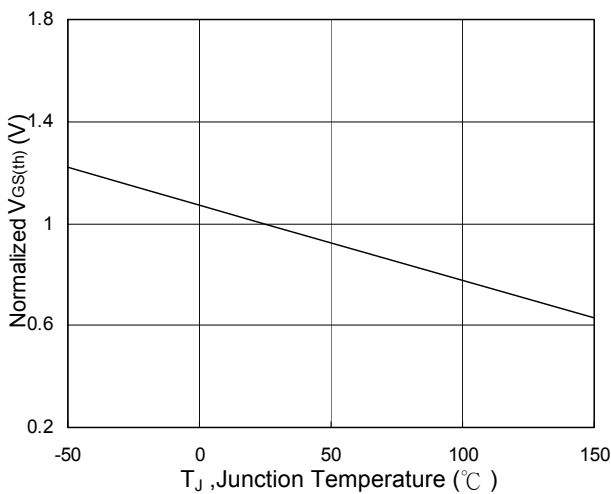
**Fig.2 On-Resistance vs. Gate-Source**



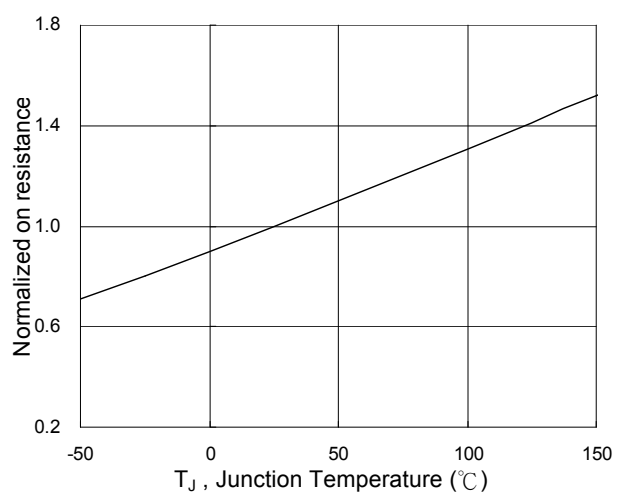
**Fig.3 Forward Characteristics Of Reverse**



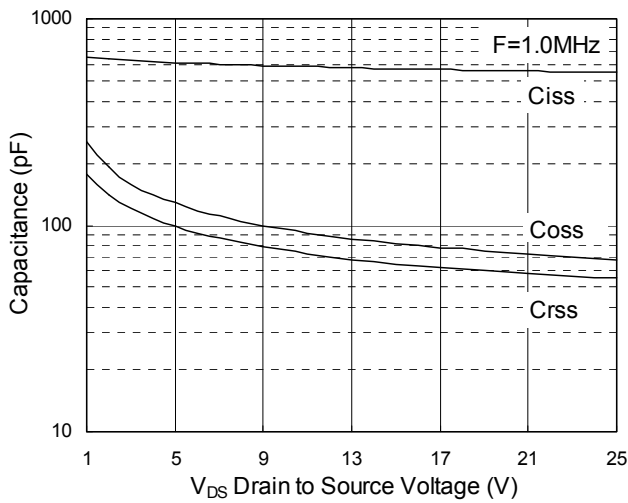
**Fig.4 Gate-Charge Characteristics**



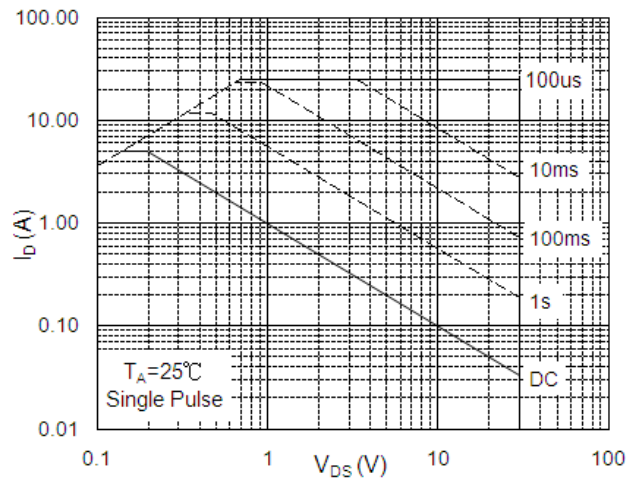
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



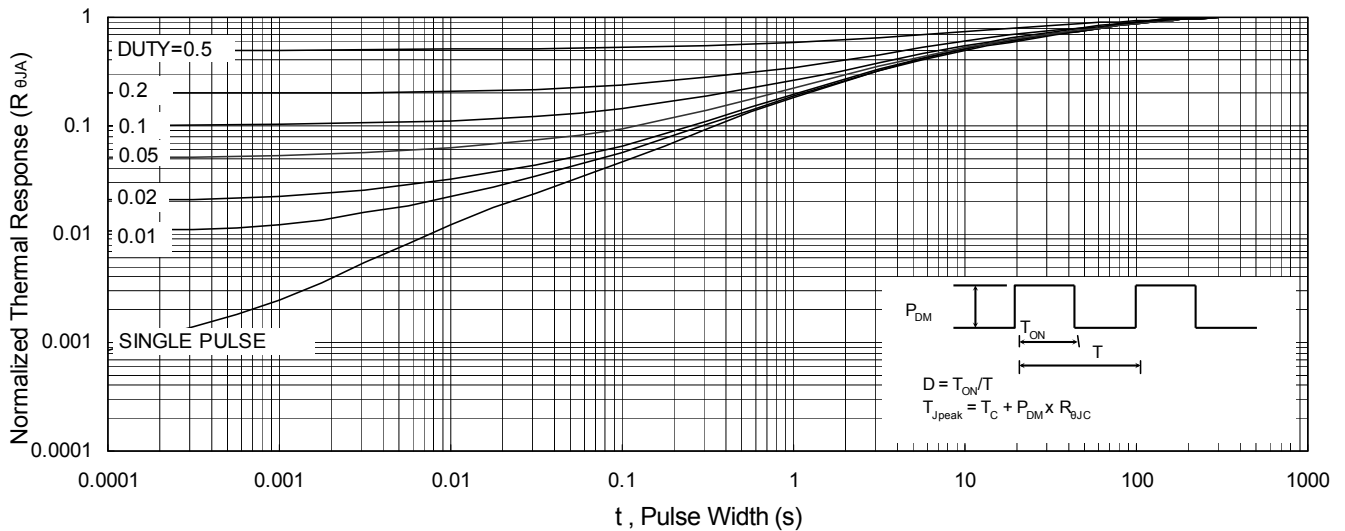
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



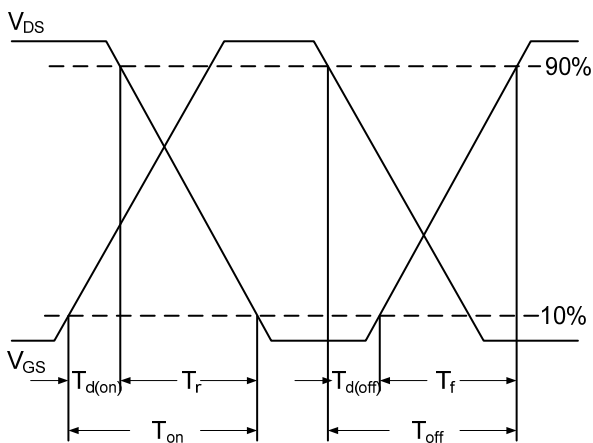
**Fig.7 Capacitance**



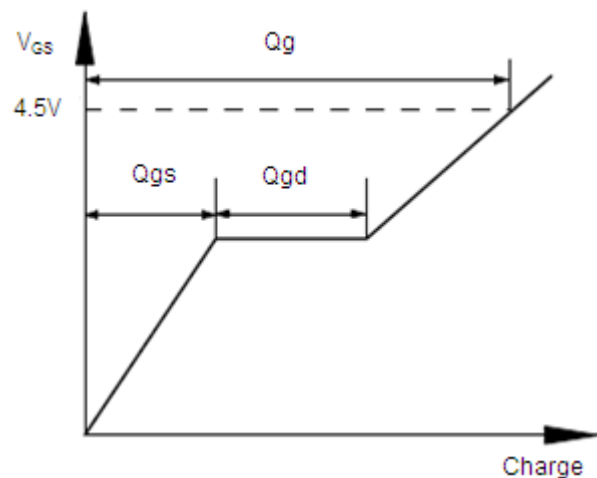
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**



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